

Specifications in this document are tentative and subject to change.

PS9505,PS9505L1,PS9505L2,PS9505L3

-NEPOC Series-2.5 A OUTPUT CURRENT, HIGH CMR, IGBT GATE DRIVE, 8-PIN DIP PHOTOCOUPLER R08DS0015EJ0001 Rev.0.01 May 12, 2010

DESCRIPTION

The PS9505, PS9505L1, PS9505L2 and PS9505L3 are optically coupled isolators containing a GaAlAs LED on the input side and a photo diode, a signal processing circuit and a power output transistor on the output side on one chip.

The PS9505 Series is designed specifically for high common mode transient immunity (CMR), high output current and high switching speed.

The PS9505 Series is suitable for driving IGBTs and MOS FETs.

The PS9505 Series is in a plastic DIP (Dual In-line Package).

The PS9505L1 is lead bending type for long creepage distance.

The PS9505L2 is lead bending type for long creepage distance (Gull-wing) for surface mount.

The PS9505L3 is lead bending type (Gull-wing) for surface mounting.

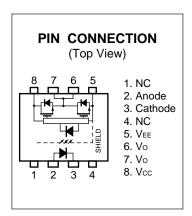
FEATURES

- Long creepage distance (8 mm MIN.: PS9505L1, PS9505L2)
- Large peak output current (2.5 A MAX., 2.0 A MIN.)
- High speed switching (tplh, tphL = 0.25 μ s MAX.)
- UVLO (Under Voltage Lock Out) protection with hysteresis
- High common mode transient immunity (CMH, CML = $\pm 25 \text{ kV}/\mu\text{s MIN.}$)
- Embossed tape product: PS9505L2-E3: 1 000 pcs/reel

: PS9505L3-E3: 1 000 pcs/reel

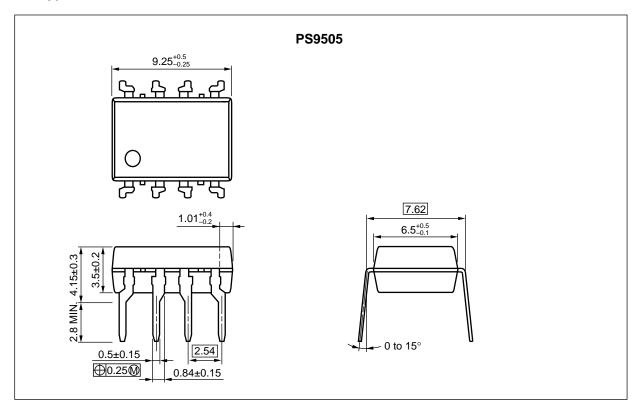
APPLICATIONS

- IGBT. Power MOS FET Gate Driver
- Industrial inverter
- IH (Induction Heating)

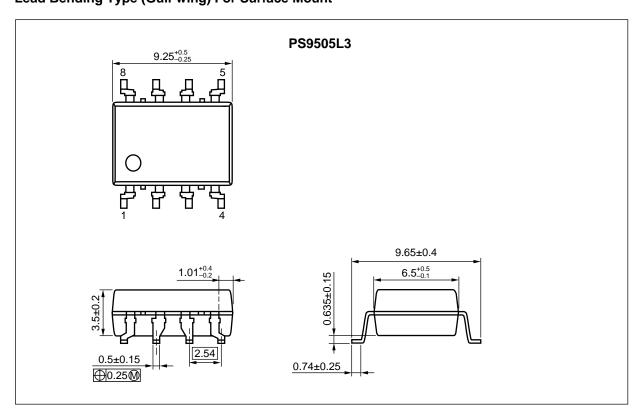


PACKAGE DIMENSIONS (UNIT: mm)

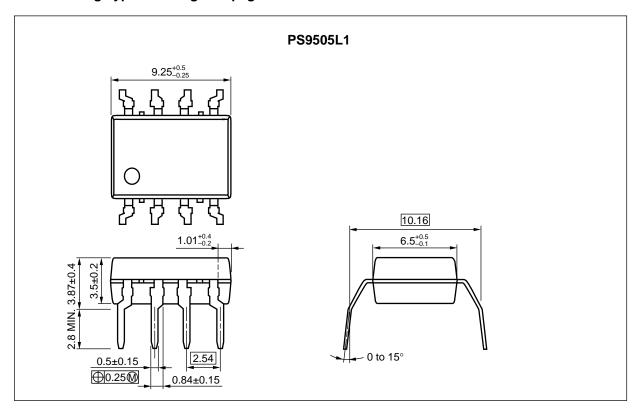
DIP Type



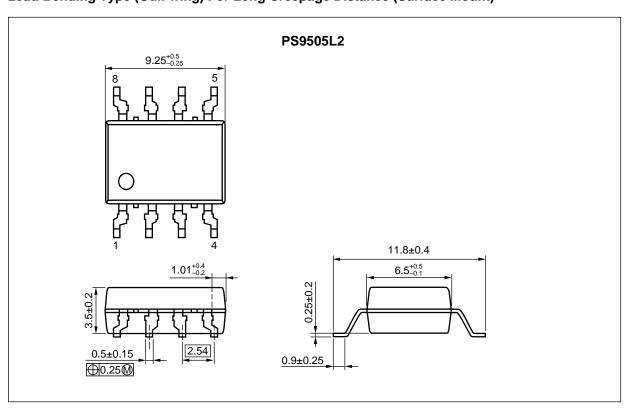
Lead Bending Type (Gull-wing) For Surface Mount



Lead Bending Type For Long Creepage Distance



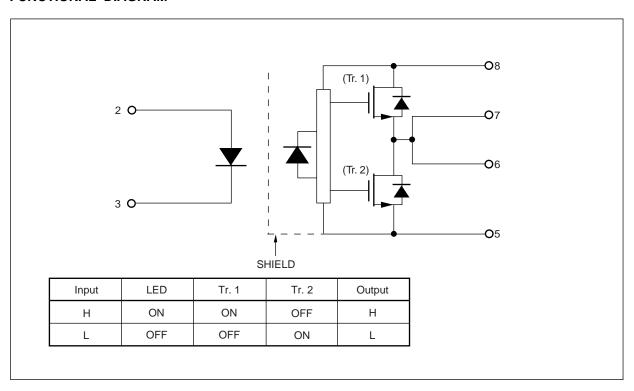
Lead Bending Type (Gull-wing) For Long Creepage Distance (Surface Mount)



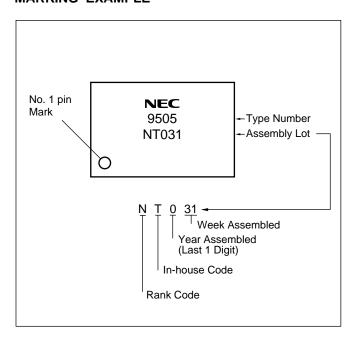
PHOTOCOUPLER CONSTRUCTION

Parameter	PS9505, PS9505L3	PS9505L1, PS9505L2
Air Distance (MIN.)	7 mm	8 mm
Outer Creepage Distance (MIN.)	7 mm	8 mm
Isolation Distance (MIN.)	0.4 mm	0.4 mm

FUNCTIONAL DIAGRAM



MARKING EXAMPLE



ABSOLUTE MAXIMUM RATINGS (TA = 25°C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit	
Diode	Forward Current	lF	25	mA	
	Peak Transient Forward Current (Pulse Width < 1 μ s)	lf (TRAN)	1.0	А	
	Reverse Voltage	VR	5	V	
Detector	High Level Peak Output Current *1	Іон (реак)	2.5	А	
	Low Level Peak Output Current *1	OL (PEAK)	2.5	А	
	Supply Voltage	(Vcc - Vee)	0 to 35	V	
	Output Voltage	Vo	0 to Vcc	V	
	Power Dissipation *2	Pc	250	mW	
Isolation Voltage *3		BV	5 000	Vr.m.s.	
Total Power Dissipation*4		Рт	300	mW	
Operating Frequency*5		f	50	kHz	
Operating Ambient Temperature		TA	-40 to +110	°C	
Storage ⁻	Temperature	T _{stg}	−55 to +125	°C	

- *1 Maximum pulse width = 10 μ s, Maximum duty cycle = 0.2%
- *2 Reduced to 4.8 mW/ $^{\circ}$ C at T_A = 70 $^{\circ}$ C or more.
- *3 AC voltage for 1 minute at T_A = 25°C, RH = 60% between input and output. Pins 1-4 shorted together, 5-8 shorted together.
- *4 Reduced to 5.4 mW/ $^{\circ}$ C at T_A = 70 $^{\circ}$ C or more.
- *5 IOH (PEAK) ≤ 2.0 A (≤ 0.3 μ s), IOL (PEAK) ≤ 2.0 A (≤ 0.3 μ s)

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	(Vcc - Vee)	15		30	V
Forward Current (ON)	IF (ON)	7	10	16	mA
Forward Voltage (OFF)	VF (OFF)	-2		0.8	V
Operating Ambient Temperature	TA	-40		110	°C

ELECTRICAL CHARACTERISTICS (Ta = -40 to +110°C, Vcc = 15 to 30 V, If (ON) = 7 to 16 mA, Vf (OFF) = -2 to 0.8 V, VEE = GND, unless otherwise specified)

Parameter		Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit
Diode	Forward Voltage	VF	IF = 10 mA, T _A = 25°C	1.2	1.56	1.8	V
	Reverse Current	IR	VR = 3 V, TA = 25°C			10	μΑ
	Input Capacitance	Cin	f = 1 MHz, V _F = 0 V, T _A = 25°C		30		pF
Detector	High Level Output Current	Іон	Vo = (Vcc-4 V)*2	0.5	2.0		Α
			Vo = (Vcc - 15 V) *3	2.0			
	Low Level Output Current	loL	Vo = (VEE + 2.5 V) *2	0.5	2.0		Α
			Vo = (VEE + 15 V) *3	2.0			
	High Level Output Voltage	Vон	lo = -100 mA ^{*4}	Vcc - 3.0	Vcc - 1.5		V
	Low Level Output Voltage	Vol	lo = 100 mA		0.1	0.5	V
	High Level Supply Current	Іссн	Vo = open, I _F = 10 mA		2.0	3.0	mA
	Low Level Supply Current	Iccl	Vo = open, V _F = 0 to +0.8 V		2.0	3.0	mA
	UVLO Threshold	Vuvlo+	Vo > 5 V, IF = 10 mA	10.8	12.3	13.4	V
		Vuvlo-		9.5	11.0	12.5	
	UVLO Hysteresis	UVLO _{HYS}	Vo > 5 V, IF = 10 mA	0.4	1.3		V
Coupled	Threshold Input Current $(L \rightarrow H)$	lflh	Io = 0 mA, Vo > 5 V		2.0	5.0	mA
	Threshold Input Voltage $(H \rightarrow L)$	V _{FHL}	Io = 0 mA, Vo < 5 V	0.8			V

^{*1} Typical values at $T_A = 25$ °C.

^{*2} Maximum pulse width = 50 μ s, Maximum duty cycle = 0.5%.

^{*3} Maximum pulse width = 10 μ s, Maximum duty cycle = 0.2%

^{*4} VoH is measured with the DC load current in this testing (Maximum pulse width = 2 ms, Maximum duty cycle = 20%).

SWITCHING CHARACTERISTICS ($T_A = -40 \text{ to } +110 ^{\circ}\text{C}$, $V_{CC} = 15 \text{ to } 30 \text{ V}$, If (ON) = 7 to 16 mA, VF (OFF) = -2 to 0.8 V, VEE = GND, unless otherwise specified)

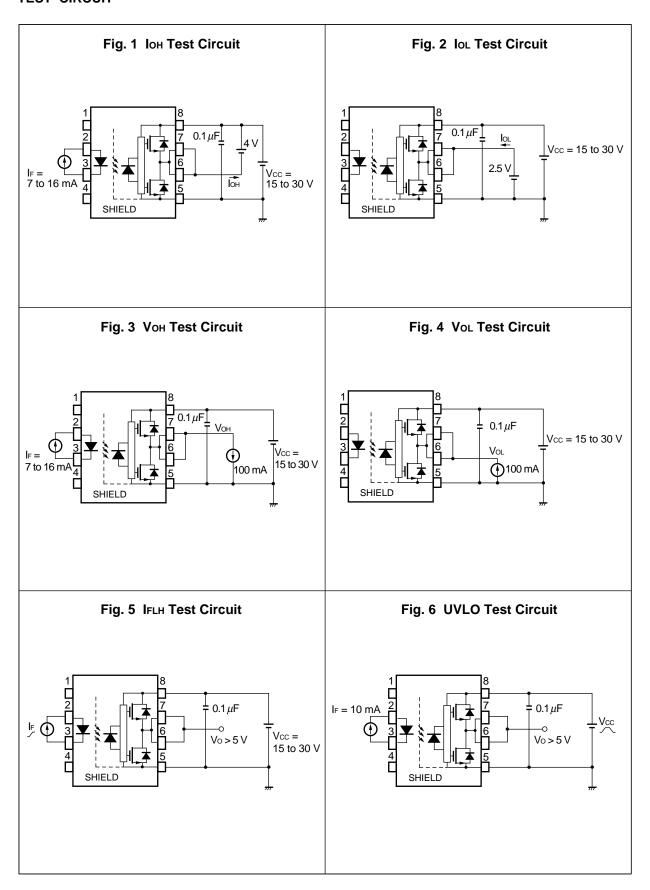
Parameter	Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit
Propagation Delay Time $(L \rightarrow H)$	t pLH	$R_g = 10 \ \Omega, \ C_g = 10 \ nF, \ f = 10 \ kHz,$		0.18	0.25	μS
Propagation Delay Time $(H \rightarrow L)$	t PHL	Duty Cycle = 50% ^{*2} , I _F = 10 mA		0.18	0.25	μS
Pulse Width Distortion (PWD)	tphl-tplh		-0.1	0.02	0.1	μS
Propagation Delay Time (Difference Between Any Two Products)	tрнц—tрцн		-0.1		0.1	μS
Rise Time	t r			50		ns
Fall Time	t _f			50		ns
UVLO (Turn On Delay)	tuvlo on	Vo > 5 V, I _F = 10 mA		0.8		μS
UVLO (Turn Off Delay)	tuvlo off	Vo < 5 V, I _F = 10 mA		0.6		μS
Common Mode Transient Immunity at High Level Output ^{*3}	[СМн]	$T_A = 25^{\circ}C$, $I_F = 10$ to 16 mA, $V_{CC} = 30$ V, $V_{O (MIN.)} = 26$ V, $V_{CM} = 1.5$ kV	25			kV/ <i>μ</i> s
Common Mode Transient Immunity at Low Level Output ^{*3}	CML	T _A = 25°C, I _F = 0 mA, V _{CC} = 30 V, V _{O (MAX.)} = 1 V, V _{CM} = 1.5 kV	25			kV/μs

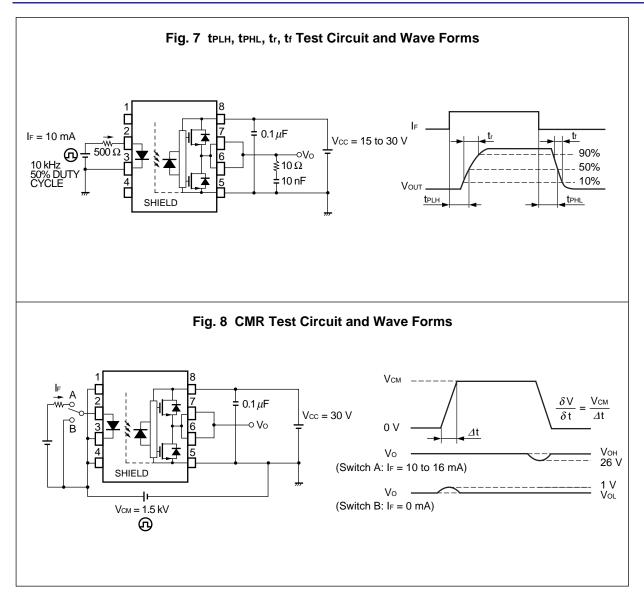
^{*1} Typical values at $T_A = 25$ °C.

^{*2} This load condition is equivalent to the IGBT load at 1 200 V/75 A.

^{*3} Connect pin 1 and pin 4 to the LED common.

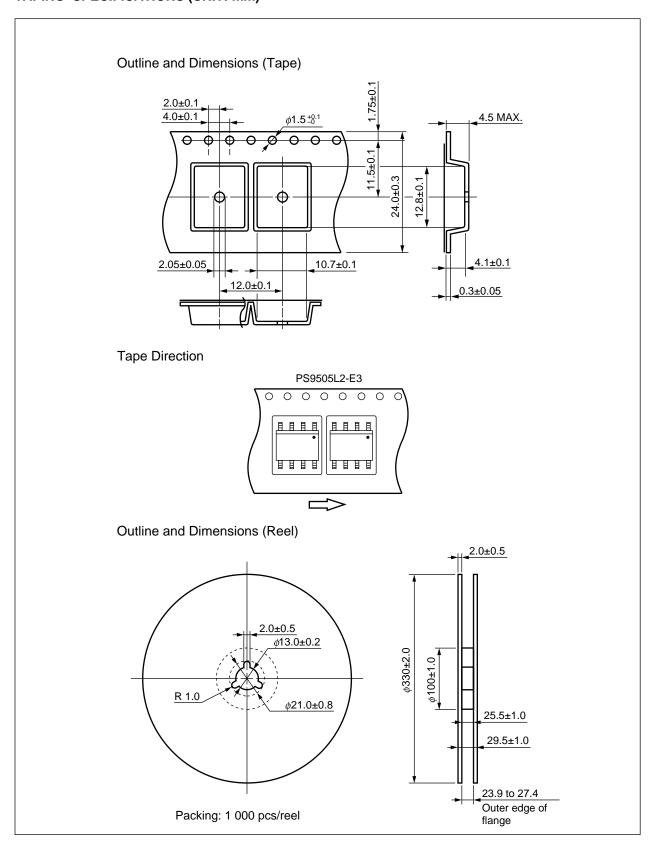
TEST CIRCUIT



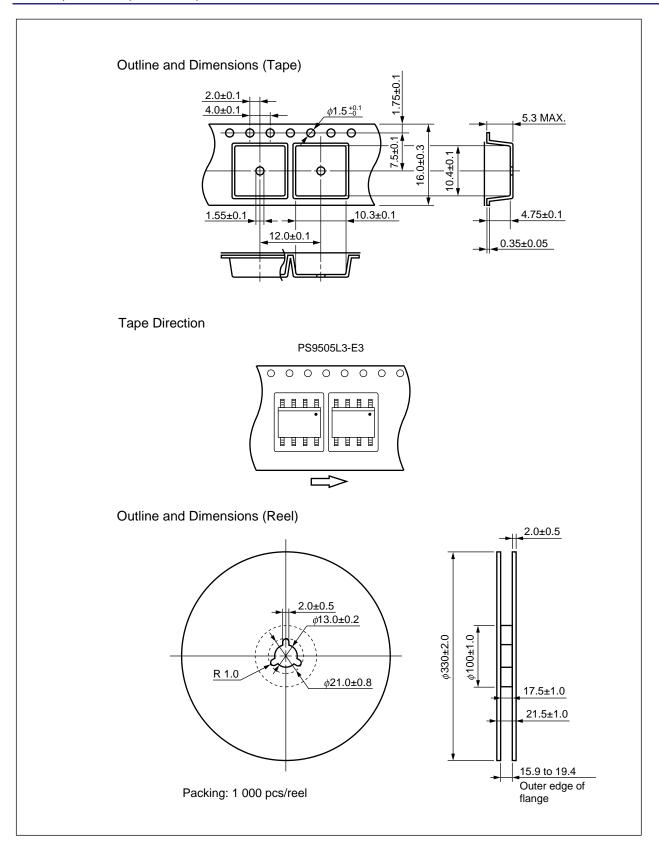


Remark CMR Test: Connect pin 1 and pin 4 to the LED common.

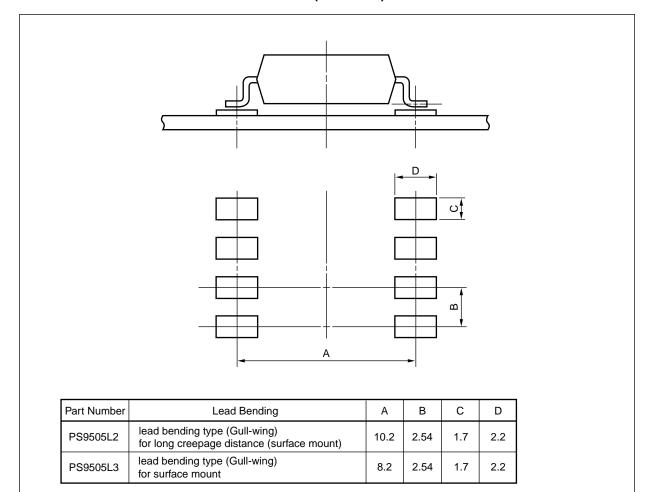
TAPING SPECIFICATIONS (UNIT: mm)



PS9505,PS9505L1,PS9505L2,PS9505L3



RECOMMENDED MOUNT PAD DIMENSIONS (UNIT: mm)



NOTES ON HANDLING

1. Recommended soldering conditions

(1) Infrared reflow soldering

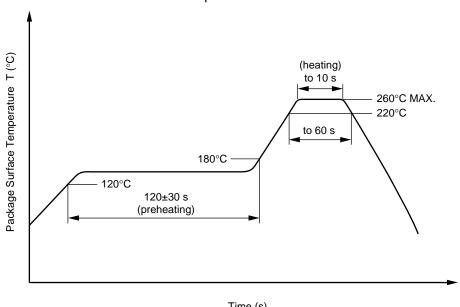
• Peak reflow temperature 260°C or below (package surface temperature)

• Time of peak reflow temperature 10 seconds or less • Time of temperature higher than 220°C 60 seconds or less

• Time to preheat temperature from 120 to 180°C 120+30 s Number of reflows Three

• Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



Time (s)

(2) Wave soldering

• Temperature 260°C or below (molten solder temperature)

• Time 10 seconds or less

· Preheating conditions 120°C or below (package surface temperature)

 Number of times One (Allowed to be dipped in solder including plastic mold portion.)

• Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content

of 0.2 Wt% is recommended.)

(3) Soldering by Soldering Iron

• Peak Temperature (lead part temperature) 350°C or below • Time (each pins) 3 seconds or less

• Flux Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt% is recommended.)

- (a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead
- (b) Please be sure that the temperature of the package would not be heated over 100°C



(4) Cautions

Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

USAGE CAUTIONS

- 1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
- 2. Board designing
 - (1) By-pass capacitor of more than 0.1 μ F is used between Vcc and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.
 - (2) In older to avoid malfunctions and characteristics degradation, IGBT collector or emitter traces should not be closed to the LED input.
 - (3) Pins 1, 4 (which is an NC^{*1} pin) can either be connected directly to the GND pin on the LED side or left open. Unconnected pins should not be used as a bypass for signals or for any other similar purpose because this may degrade the internal noise environment of the device.
 - *1 NC: Non-Connection (No Connection)
- 3. Make sure the rise/fall time of the forward current is 0.5 μ s or less.
- **4.** In order to avoid malfunctions, make sure the rise/fall slope of the supply voltage is $3 \text{ V}/\mu\text{s}$ or less.
- **5.** Avoid storage at a high temperature and high humidity.



Caution

GaAs Products

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
 - Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
- 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.

Revision History

PS9505,PS9505L1,PS9505L2,PS9505L3 Preliminary Data Sheet

		Description		
Rev.	Date	Page	Summary	
0.01	May 12, 2010	-	First Edition issued	